

# MOSFET – N-Channel, Field Effect Transistor, Enhancement Mode

## NDP6060 / NDB6060

### General Description

These N-Channel enhancement mode power field effect transistors are produced using onsemi's proprietary, high cell density, DMOS technology. This very high density process has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as automotive, DC/DC converters, PWM motor controls, and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

### Features

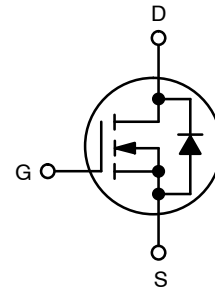
- 48 A, 60 V
  - ♦  $R_{DS(ON)} = 0.025 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$
- Critical DC Electrical Parameters Specified at Elevated Temperature
- Rugged Internal Source-Drain Diode Can Eliminate the Need for an External Zener Diode Transient Suppressor
- 175°C Maximum Junction Temperature Rating
- High Density Cell Design for Extremely Low  $R_{DS(ON)}$
- TO-220 Package for Both Through Hole and Surface Mount Applications
- This is a Halide Free Device

### MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

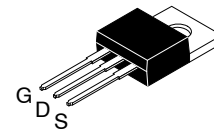
Symbol	Rating	NDP6060	Unit
$V_{DSS}$	Drain-Source Voltage	60	V
$V_{DGR}$	Drain-Gate Voltage ( $R_{GS} \leq 1 \text{ M}\Omega$ )	60	V
$V_{GSS}$	Drain-Source Voltage - Continuous - Nonrepetiti ( $t_p < 50 \mu\text{s}$ )	$\pm 20$ $\pm 40$	V
$I_D$	Drain Current - Continuous $T_C = 25^\circ\text{C}$ - Continuous $T_C = 100^\circ\text{C}$ - Pulsed	48 32 144	A
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$ - Derate above $25^\circ\text{C}$	100 0.67	W W/°C
$T_J, T_{STG}$	Operating and Storage Temperature Range	-65 to 175	°C
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	275	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

$V_{DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
60 V	0.025 m $\Omega$ @ 10 V	48 A

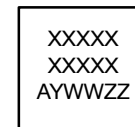


N-CHANNEL MOSFET



TO-220-3LD  
CASE 340AT

### MARKING DIAGRAM



XXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
ZZ = Assembly Lot Code

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NDP6060	TO-220-3LD (Halide Free)	800 / Units / Tube

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

# NDP6060 / NDB6060

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
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### DRAIN-SOURCE AVALANCHE RATINGS (Note 1)

W <sub>DSS</sub>	Single Pulse Drain-Source Avalanche Energy	V <sub>DD</sub> = 25 V, I <sub>D</sub> = 48 A	-	-	200	mJ
I <sub>AR</sub>	Maximum Drain-Source Avalanche Current		-	-	48	A

### OFF CHARACTERISTICS

BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	60	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	-	-	250	μA
		T <sub>J</sub> = 125°C	-	-	1	mA
I <sub>GSSF</sub>	Gate-Body Leakage, Forward	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V	-	-	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	V <sub>GS</sub> = -20 V, V <sub>DS</sub> = 0 V	-	-	-100	nA

### ON CHARACTERISTICS (Note 1)

V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2	2.9	4	V
		T <sub>J</sub> = 125°C	1.4	2.3	3.6	
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 24 A	-	0.02	0.025	W
		T <sub>J</sub> = 125°C	-	0.032	0.04	
I <sub>D(on)</sub>	On-State Drain Current	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 10 V	48	-	-	A
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 24 A	10	19	-	S

### DYNAMIC CHARACTERISTICS

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz	-	1190	1800	pF
C <sub>oss</sub>	Output Capacitance		-	475	800	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	150	400	pF

### SWITCHING CHARACTERISTICS (Note 1)

t <sub>D(on)</sub>	Turn - On Delay Time	V <sub>DD</sub> = 30 V, I <sub>D</sub> = 48 A, V <sub>GS</sub> = 10 V, R <sub>GEN</sub> = 7.5 W	-	10	20	nS
t <sub>r</sub>	Turn - On Rise Time		-	145	300	nS
t <sub>D(off)</sub>	Turn - Off Delay Time		-	28	60	nS
t <sub>f</sub>	Turn - Off Fall Time		-	77	150	nS
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 48 V, I <sub>D</sub> = 48 A, V <sub>GS</sub> = 10 V	-	39	70	nC
Q <sub>gs</sub>	Gate-Source Charge		-	7.6	-	nC
Q <sub>gd</sub>	Gate-Drain Charge		-	22	-	nC

### DRAIN-SOURCE DIODE CHARACTERISTICS

I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current		-	-	48	A
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		-	-	144	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 24 A (Note 1)	-	0.9	1.3	V
		T <sub>J</sub> = 125°C	-	0.8	1.2	
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>F</sub> = 48 A,	35	87	140	ns
I <sub>rr</sub>	Reverse Recovery Current	dI <sub>F</sub> /dt = 100 A/μs	2	3.6	8	A

### THERMAL CHARACTERISTICS

R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case		-	-	1.5	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient		-	-	62.5	°C/W

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

TYPICAL CHARACTERISTICS

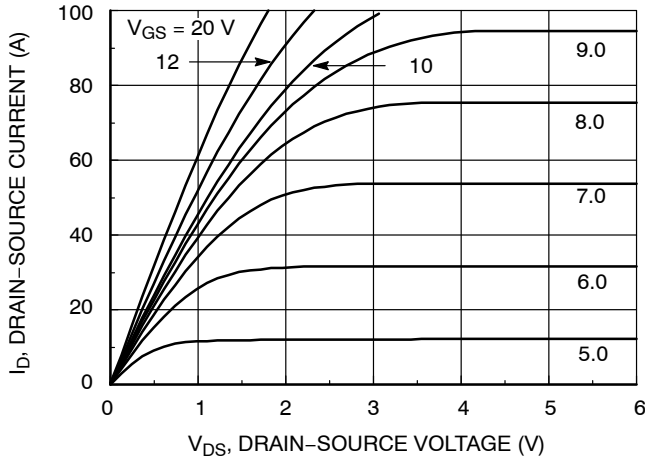


Figure 1. On-Region Characteristics

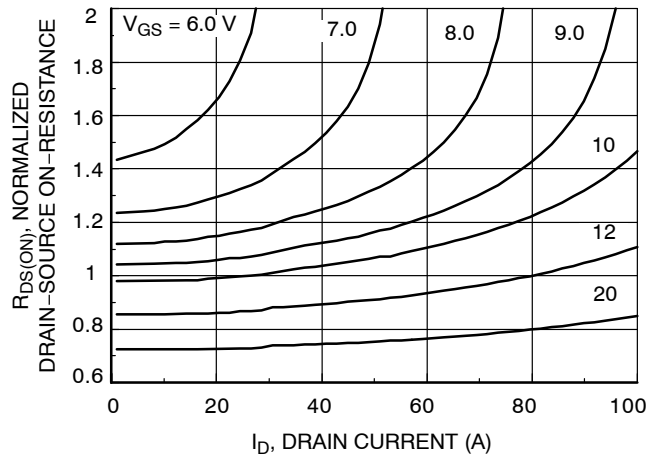


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

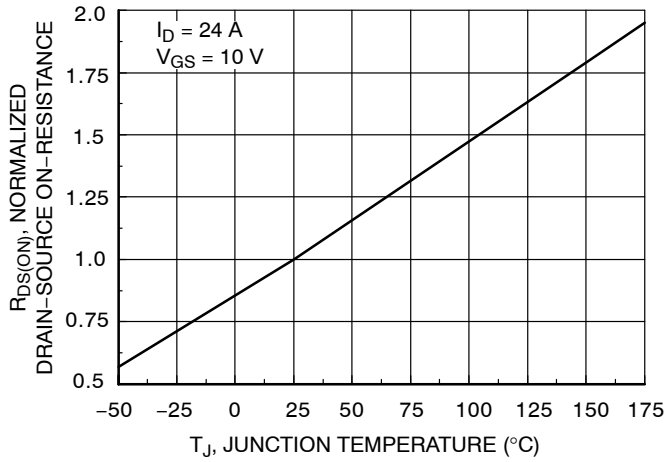


Figure 3. On-Resistance Variation with Temperature

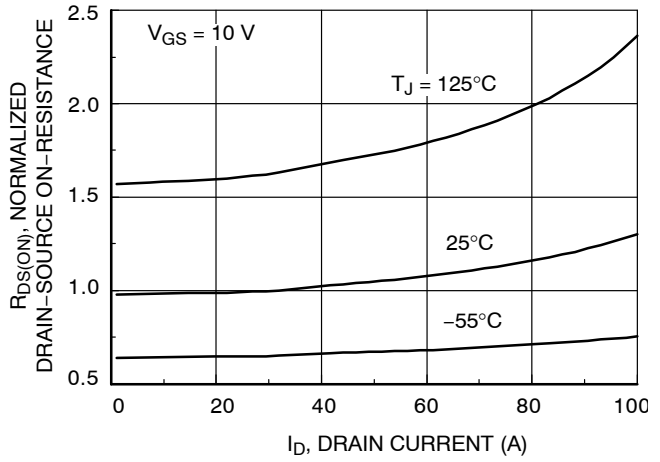


Figure 4. On-Resistance Variation with Drain Current and Temperature

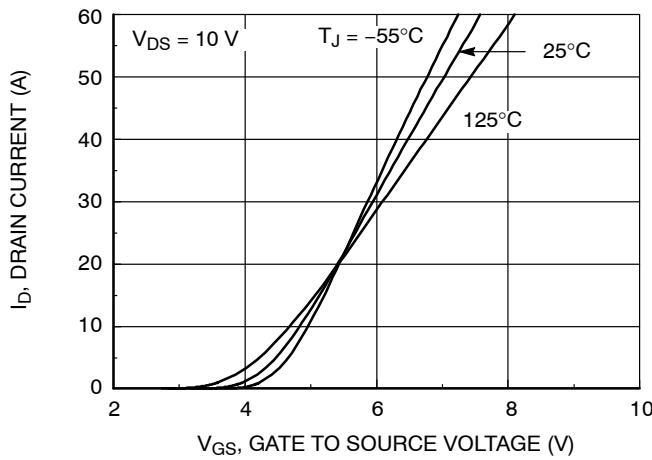


Figure 5. Transfer Characteristics

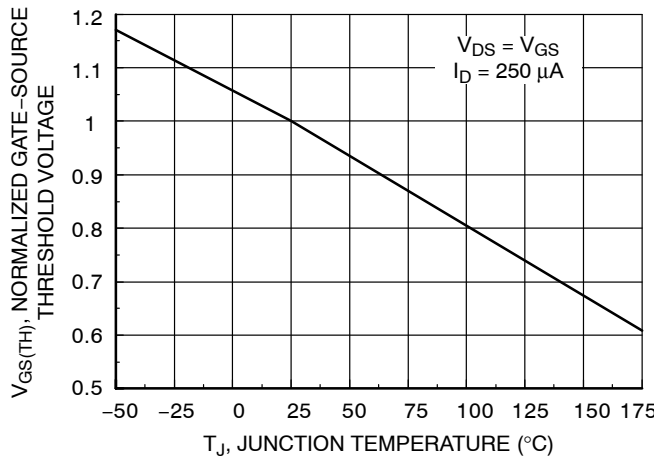


Figure 6. Gate Threshold Variation with Temperature

TYPICAL CHARACTERISTICS (continued)

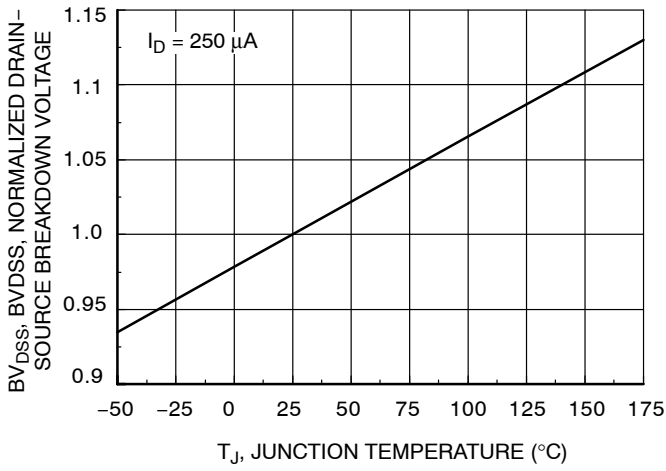


Figure 7. Breakdown Voltage Variation with Temperature

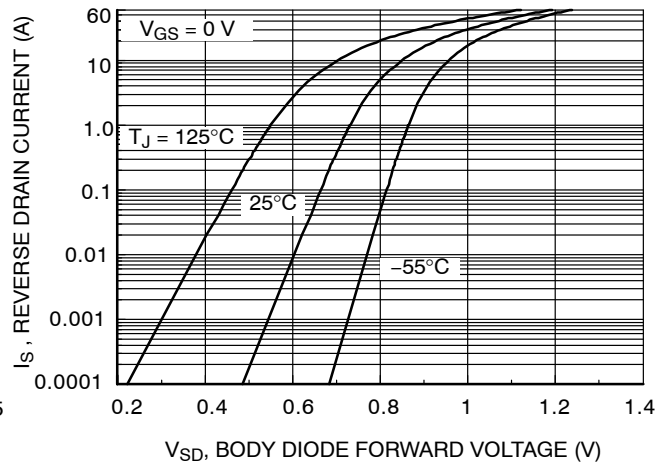


Figure 8. Body Diode Forward Voltage Variation with Current and Temperature

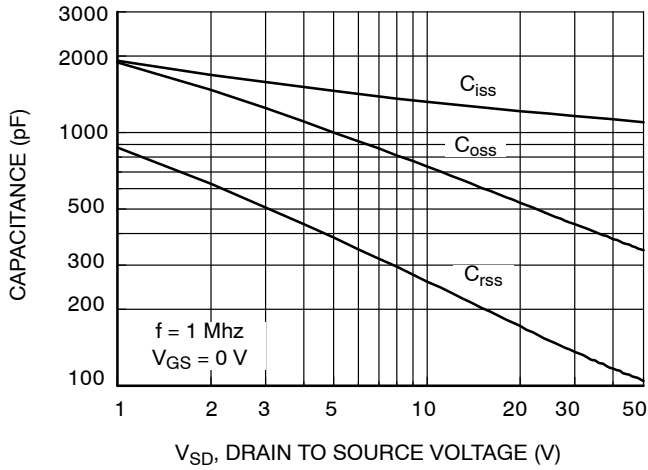


Figure 9. Capacitance Characteristics

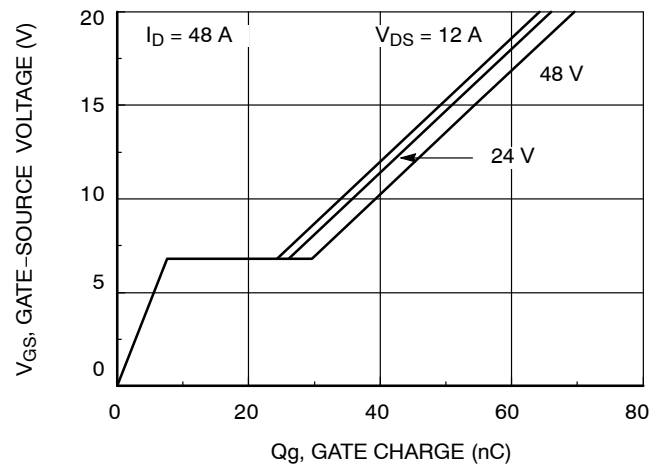


Figure 10. Gate Charge Characteristics

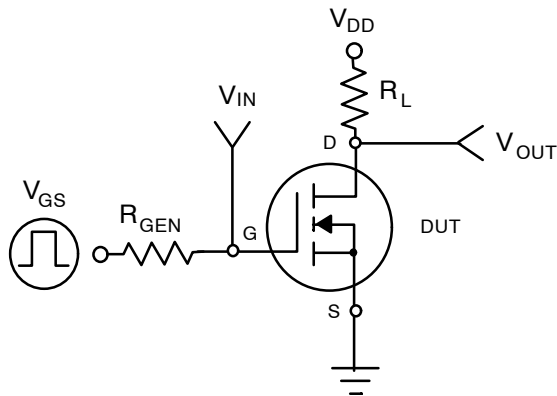


Figure 11. Switching Test Circuit

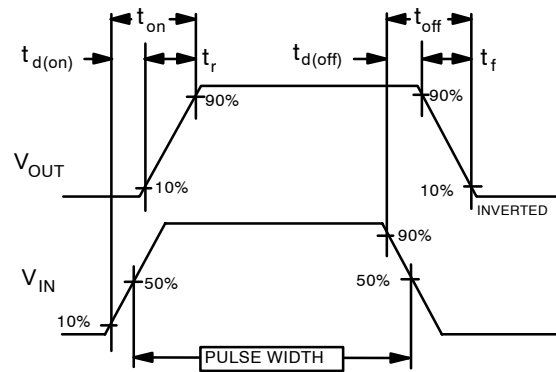


Figure 12. Switching Waveforms

TYPICAL CHARACTERISTICS

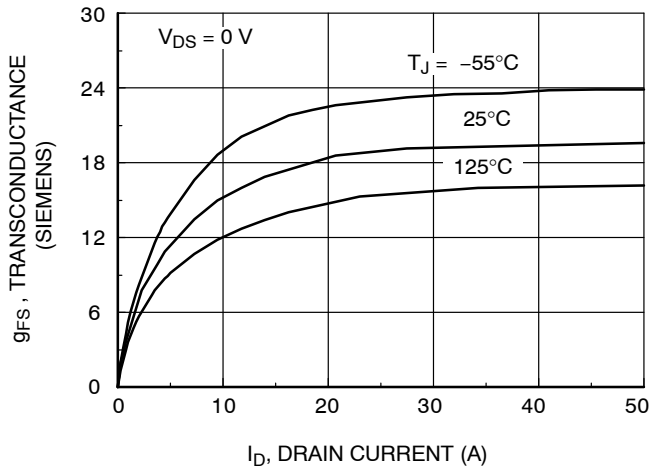


Figure 13. Transconductance Variation with Drain Current and Temperature

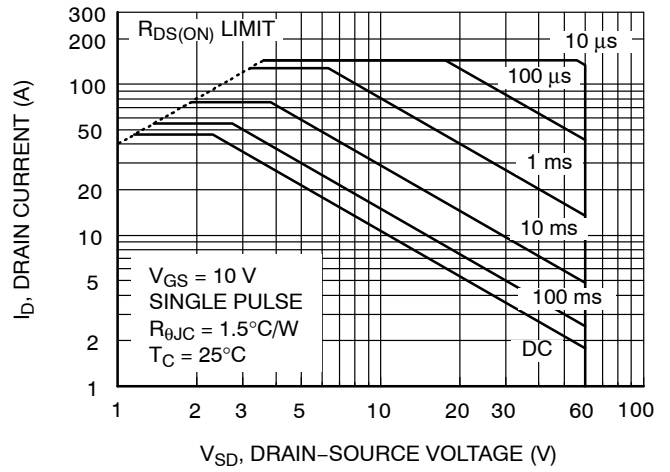


Figure 14. Maximum Safe Operating Area

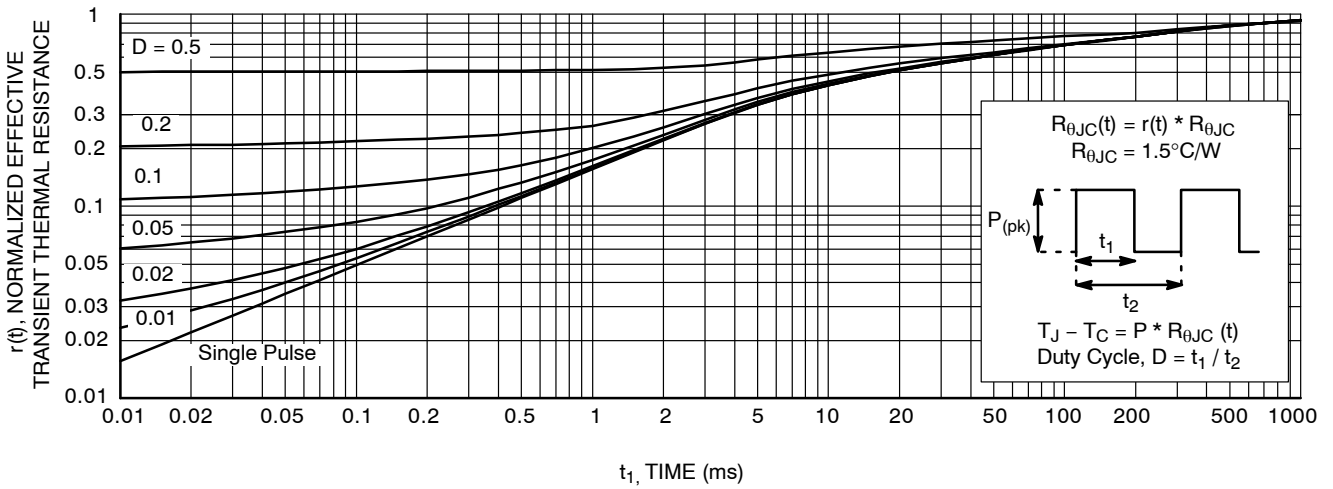
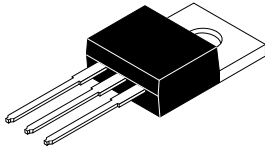


Figure 15. Transient Thermal Response Curve

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



Scale 1:1

### TO-220-3LD CASE 340AT ISSUE A

DATE 03 OCT 2017



- NOTES:
- A) REFERENCE JEDEC, TO-220, VARIATION AB
  - B) ALL DIMENSIONS ARE IN MILLIMETERS.
  - C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [ ].
  - D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
  - E) DOES NOT COMPLY JEDEC STANDARD VALUE.
  - F) "A1" DIMENSIONS AS BELOW:  
 SINGLE GAUGE = 0.51 - 0.61  
 DUAL GAUGE = 1.10 - 1.45
  - G) PRESENCE IS SUPPLIER DEPENDENT
  - H) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.

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